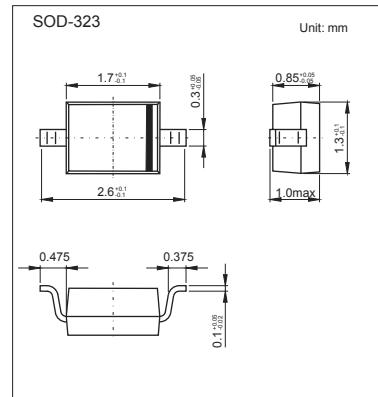


Schottky Diodes

1KK2301F

■ Features

- High current rectifier Schottky diode
- Low voltage, low inductance
- For power supply
- For detection and step-up-conversion



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Non-Repetitive Peak reverse voltage	V _{RM}	10	V
Forward current	I _F	3	A
Forward surge Current tp=10ms	I _{FSM}	5	A
Total power dissipation Ts ≤ 28°C	P _{tot}	1350	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{STG}	-65 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Forwarad voltage (Note 1)	V _F	I _F =10mA I _F =100mA I _F =500mA I _F =1000mA			300 380 500 600	mV
Leakage current	I _R	V _R = 5 V V _R = 8 V			1 5 2 5	μ A
Junction Capacitance	C _J	V _R =5V,f=1.0MHz			30	pF

Note1 : Pulsed test: tp = 300 μs; D = 0.01

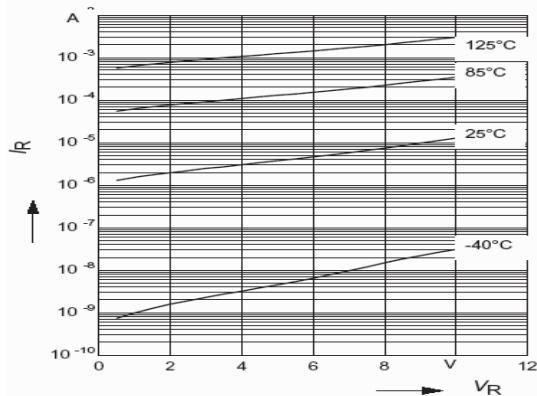
■ Marking

Marking	SL
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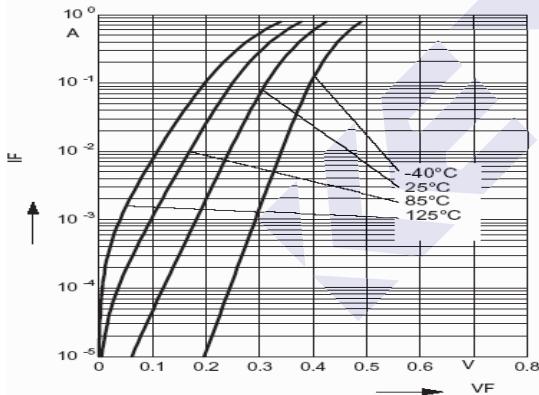
1KK2301F

■ Typical Characteristics

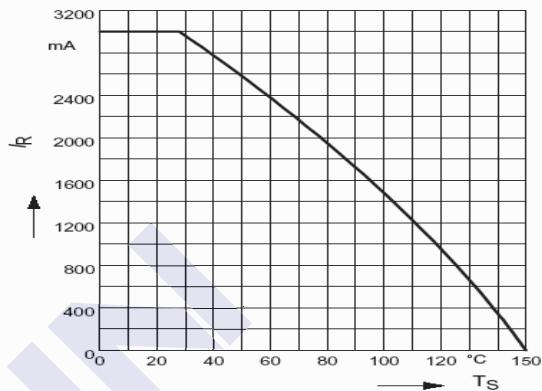
Reverse current $I_R = f(V_R)$
 $T_A = \text{Parameter}$



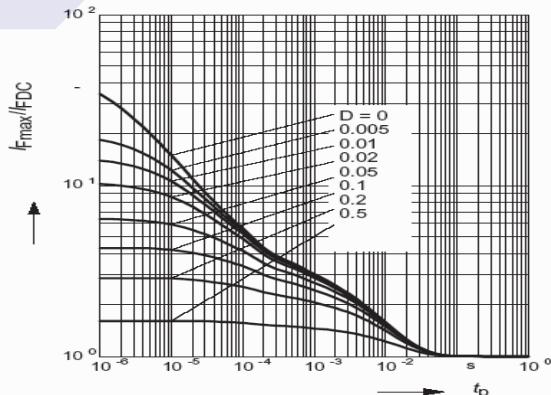
Forward current $I_F = f(V_F)$
 $T_A = \text{Parameter}$



Forward current $I_F = f(T_S)$



Permissible Pulse Load
 $I_{F\max}/I_{FDC} = f(t_p)$



Permissible Puls Load $R_{thJS} = f(t_p)$

